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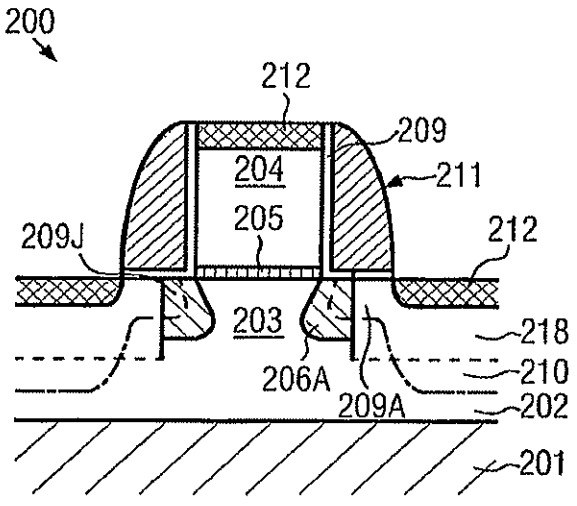
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(54) Title: TRANSISTOR DEVICE HAVING AN INCREASED THRESHOLD STABILITY WITHOUT DRIVE CURRENT DEGRADATION



(57) Abstract: By removing a portion of a halo region (206, 306) or by avoiding the formation of the halo region (206, 306) within the extension region (209A), which may be subsequently formed on the basis of a re-grown semiconductor material (218, 318), the threshold roll off behavior may be significantly improved, wherein an enhanced current drive capability may simultaneously be achieved.

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